

MOS FIELD EFFECT TRANSISTOR 2SK3454

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SK3454 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for high voltage applications such as DC/DC converter.

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3454	Isolated TO-220

FEATURES

- •Gate voltage rating ±30 V
- •Low on-state resistance

 $R_{DS(on)} = 0.63 \Omega MAX. (Vgs = 10 V, ID = 4.0 A)$

•Low input capacitance

Ciss = 400 pF TYP. (VDS = 10 V, VGS = 0 V)

- •Built-in gate protection diode
- •Isolated TO-220 package

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Drain to Source Voltage (Vgs = 0 V)	Vpss	250	V
Diani to course voltage (ves = 0 v)	V D33	200	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±30	V
Drain Current(DC) (Tc = 25°C)	ID(DC)	±7.0	Α
Drain Current(pulse) Note1	D(pulse)	±21	Α
Total Power Dissipation (T _A = 25°C)	P _{T1}	2.0	W
Total Power Dissipation (Tc = 25°C)	P _{T2}	30	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note2	las	7.0	Α
Single Avalanche Energy Note2	Eas	49	mJ

Notes1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 125 V, R_G = 25 Ω , V_{GS} = 20 V \rightarrow 0 V

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

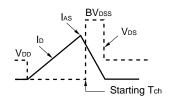


ELECTRICAL CHARACTERISTICS (TA = 25°C)

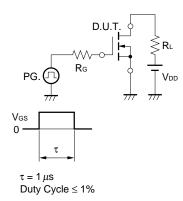
Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain Leakage Current	Ioss	V _{DS} = 250 V, V _{GS} = 0 V			100	μΑ
Gate Leakage Current	Igss	Vgs = ±30 V, Vps = 0 V			±10	μΑ
Gate to Source Cut-off Voltage	V _G S(off)	V _{DS} = 10 V, I _D = 1 mA	2.5		4.5	V
Forward Transfer Admittance	yfs	V _{DS} = 10 V, I _D = 4.0 A	1.0			S
Drain to Source On-state Resistance	R _{DS(on)}	Vgs = 10 V, ID = 4.0 A		0.5	0.63	Ω
Input Capacitance	Ciss	V _{DS} = 10 V		400		pF
Output Capacitance	Coss	Vgs = 0 V		110		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		55		pF
Turn-on Delay Time	T _{d(on)}	V _{DD} = 125 V, I _D = 4.0 A		11		ns
Rise Time	Tr	V _{GS(on)} = 10 V		18		ns
Turn-off Delay Time	T _{d(off)}	R _G = 10 Ω		32		ns
Fall Time	Tf			15		ns
Total Gate Charge	Q _G	V _{DD} = 200 V		18		nC
Gate to Source Charge	Qgs	Vgs = 10 V		3.5		nC
Gate to Drain Charge	Q _{GD}	ID = 7.0 A		10		nC
Diode Forward Voltage	VF(S-D)	IF = 7.0 A, VGS = 0 V		1.0		V
Reverse Recovery Time	Trr	IF = 7.0 A, VGS = 0 V		250		ns
Reverse Recovery Charge	Qrr	di/dt = 50 A/μs		1.0		μC

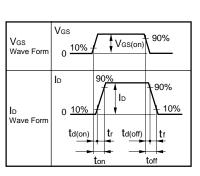
TEST CIRCUIT 1 AVALANCHE CAPABILITY

$\begin{array}{c|c} \text{D.U.T.} \\ \text{RG} = 25 \ \Omega \\ \text{PG.} \\ \hline \\ \text{VGS} = 20 \rightarrow 0 \ V \\ \end{array} \begin{array}{c} \text{D.U.T.} \\ \\ \text{FG.} \\ \hline \\ \end{array} \begin{array}{c} \text{VDD} \\ \\ \end{array}$

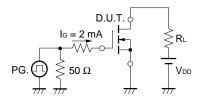


TEST CIRCUIT 2 SWITCHING TIME

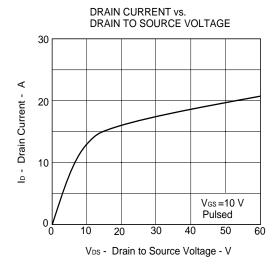


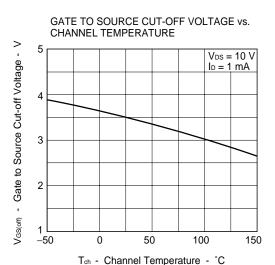


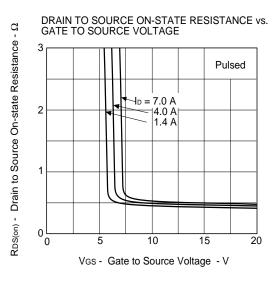
TEST CIRCUIT 3 GATE CHARGE

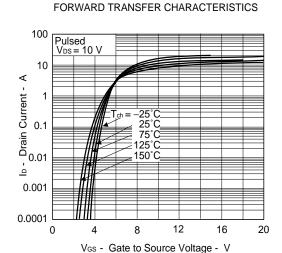


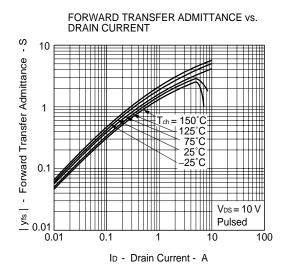
T中间"AEKHAR"A芯框南STICS

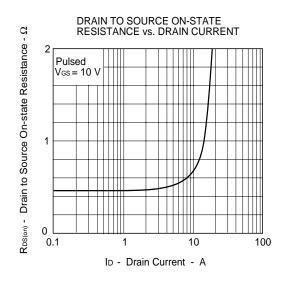


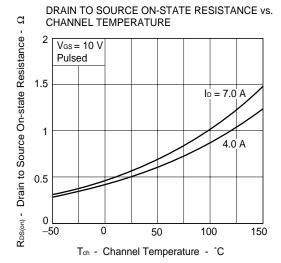


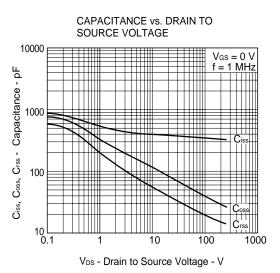


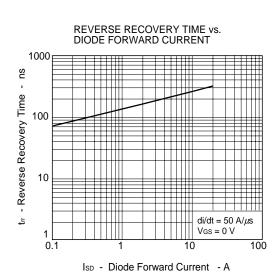


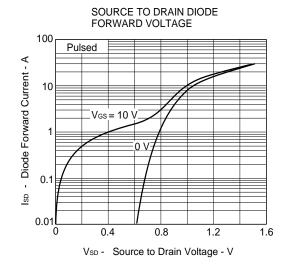


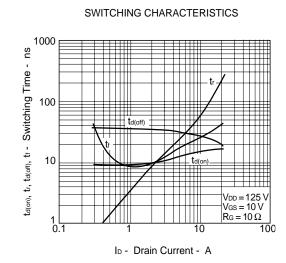


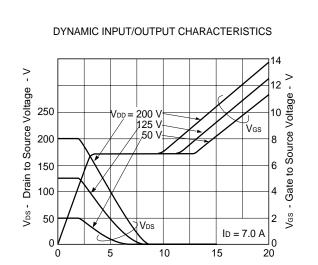












Qg - Gate Charge - nC

20

0

0

20

40 60

查询"2SK3454"供应商



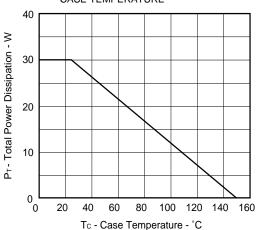
80

Tch - Channel Temperature - °C

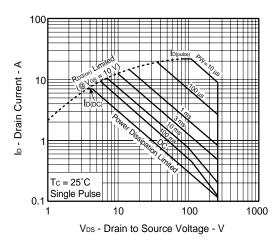
100 120 140 160

DERATING FACTOR OF FORWARD BIAS

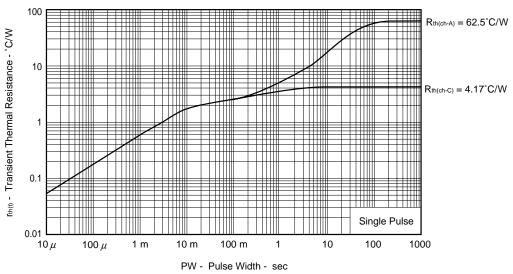
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



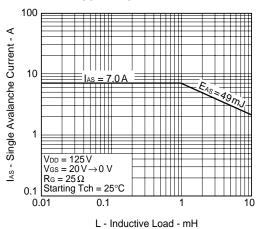
FORWARD BIAS SAFE OPERATING AREA



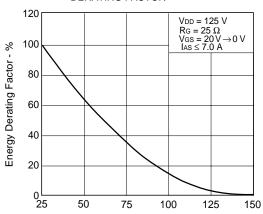
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD

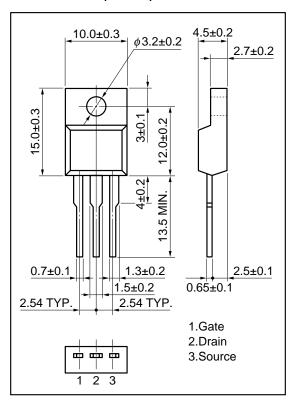


SINGLE AVALANCHE ENERGY DERATING FACTOR

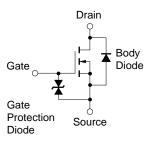


Starting T $_{\text{ch}}$ - Starting Channel Temperature - $^{\circ}\text{C}$

Isolated TO-220 (MP-45F)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

7



- The information in this document is current as of May, 2001. The information is subject to change without notice. For actual design-in, refer to the latest publications of NEC's data sheets or data books, etc., for the most up-to-date specifications of NEC semiconductor products. Not all products and/or types are available in every country. Please check with an NEC sales representative for availability and additional information.
- No part of this document may be copied or reproduced in any form or by any means without prior written consent of NEC. NEC assumes no responsibility for any errors that may appear in this document.
- NEC does not assume any liability for infringement of patents, copyrights or other intellectual property rights of
 third parties by or arising from the use of NEC semiconductor products listed in this document or any other
 liability arising from the use of such products. No license, express, implied or otherwise, is granted under any
 patents, copyrights or other intellectual property rights of NEC or others.
- Descriptions of circuits, software and other related information in this document are provided for illustrative purposes in semiconductor product operation and application examples. The incorporation of these circuits, software and information in the design of customer's equipment shall be done under the full responsibility of customer. NEC assumes no responsibility for any losses incurred by customers or third parties arising from the use of these circuits, software and information.
- While NEC endeavours to enhance the quality, reliability and safety of NEC semiconductor products, customers
 agree and acknowledge that the possibility of defects thereof cannot be eliminated entirely. To minimize
 risks of damage to property or injury (including death) to persons arising from defects in NEC
 semiconductor products, customers must incorporate sufficient safety measures in their design, such as
 redundancy, fire-containment, and anti-failure features.
- NEC semiconductor products are classified into the following three quality grades:
 - "Standard", "Special" and "Specific". The "Specific" quality grade applies only to semiconductor products developed based on a customer-designated "quality assurance program" for a specific application. The recommended applications of a semiconductor product depend on its quality grade, as indicated below. Customers must check the quality grade of each semiconductor product before using it in a particular application.
 - "Standard": Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
 - "Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
 - "Specific": Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems and medical equipment for life support, etc.

The quality grade of NEC semiconductor products is "Standard" unless otherwise expressly specified in NEC's data sheets or data books, etc. If customers wish to use NEC semiconductor products in applications not intended by NEC, they must contact an NEC sales representative in advance to determine NEC's willingness to support a given application.

(Note)

- (1) "NEC" as used in this statement means NEC Corporation and also includes its majority-owned subsidiaries.
- (2) "NEC semiconductor products" means any semiconductor product developed or manufactured by or for NEC (as defined above).

M8E 00.4